

AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A bonding structure for a cemented carbide element and a diamond element comprising:

a cemented carbide element formed by a cemented carbide;

a diamond element formed by a diamond; and

a bonding layer that is formed between the cemented carbide element and the diamond element in order to bond them;

wherein said bonding layer includes a diffusion layer in which at least one or two or more metals selected from a group consisting of Fe, Ni, Co, Ti, Zr, W, V, Nb, Ta, Cr, Mo, and Hf diffuses into at least one of said cemented carbide or said diamond; and

wherein a cross-section in a transverse direction of said bonding layer is line analyzed using EPMA, the maximum value of a content of said metals in said cross section is 20 times or greater than an average value of a content of said metals in a region of the cemented carbide element not influenced by the diffusion, and 100 times or greater than an average value of a content of said metal in a region of said diamond element not influenced by the diffusion.

2. (Original) A bonding structure for a cemented carbide element and a diamond element according to claim 1, wherein said bonding layer includes a diffusion layer in which at least one of Fe and Ni diffuses into said diamond.

3. (Previously Presented) A bonding structure for a cemented carbide element and a diamond element, comprising:

a cemented carbide element formed by a cemented carbide;

a diamond element formed by a diamond; and

a bonding layer that is formed between the cemented carbide element and the diamond element in order to bond them;

wherein said bonding layer includes a Co layer, and

at least on a diamond side of said Co layer, a diffusion layer in which Co diffuses into said diamond.

4. (Original) A bonding structure for a cemented carbide element and a diamond element according to claim 1, wherein said bonding layer includes a diffusion layer in which one or two or more metals selected from a group consisting of Ti, Zr, W, V, Nb, Ta, Cr, Mo, and Hf diffuses into at least one of said cemented carbide or said diamond.

5. (Original) A bonding structure for a cemented carbide element and a diamond element according to claim 1, wherein said diamond is a high heat resistant sintered diamond including a binder phase of 0.1 to 15% by volume, where said binder phase is formed by one or two or more selected from the group consisting of carbonates of Mg, Ca, Sr, and Ba, oxides of Mg, Ca, Sr, and Ba, complex carbonates and complex oxide containing two or more thereof.

6. (Canceled)

7. (Withdrawn) A bonding method for a cemented carbide element and a diamond element, comprising the steps of

interposing a metal material including one or two or more metals selected from a group consisting of Fe, Ni, Co, Ti, Zr, W, V, Nb, Ta, Cr, Mo, and Hf between the cemented carbide element and the diamond element; and

heating said cemented carbide element, said diamond element, and said metal material, forming a diffusion layer in which said metal diffuses into at least one of said cemented carbide element or said diamond element, and bonding said cemented carbide element and said diamond element.

8. (Withdrawn) A bonding method for a cemented carbide element and a diamond element according to claim 7, wherein said metal material includes at a total of 70% by mass, at least one of Fe and Ni, and in the step for bonding said cemented carbide element and said diamond

element, said heating is carried out under conditions A (K) and B (GPa) that satisfy the following two equations simultaneously, and a diffusion layer is formed by at least one of Fe and Ni diffusing into the diamond:

A > 1175

$$B > 0.0027 \times A + 0.81$$

9. (Withdrawn) A bonding method for a cemented carbide element and a diamond element according to claim 7, wherein said metal material includes Co at 70% by mass or greater, and in the step of bonding said cemented carbide element and said diamond element, said heating is carried out under conditions A (K) and B (GPa) that satisfy the following two equations simultaneously, a diffusion layer is formed by Co diffusing into said cemented carbide, and a Co layer is formed.

$$A > 1175$$

$$B > 0.0027 \times A + 0.81$$

10. (Withdrawn) A bonding method for a cemented carbide element and a diamond element according to claim 7, wherein said metal material includes at 70% by mass or greater one or two or more of the metals selected from the group consisting of Ti, Zr, W, V, Nb, Ta, Cr, Mo, or Hf, and in the step of bonding said cemented carbide element and said diamond element, said heating is carried out under conditions A (K) and B (GPa) that satisfy the following two equations simultaneously, and a diffusion layer is formed by said metal diffusing into at least one of said cemented carbide or said diamond.

$$A > 1175$$

$$B > 0.0027 \times A + 0.81$$

14. (Withdrawn) A cutting tip for a drilling tool, comprising:

a cemented carbide cutting base mounted on a post of the tool body of the drilling tool;

a diamond element supported by said cutting base; and

a bonding layer formed between said cutting base and said diamond element in order to bond them;

wherein said bonding layer includes a diffusion layer in which one or two or more metals selected from a group consisting of Fe, Ni, Co, Ti, Zr, W, V, Nb, Ta, Cr, Mo, and Hf diffuses onto at least one of said cemented carbide or said diamond.

15. (Withdrawn) A cutting tip according to claim 14, wherein said bonding layer includes a diffusion layer in which at least one of Fe and Ni diffuse into said diamond.

16. (Withdrawn) A cutting tip according to claim 14, wherein said bonding layer includes a diffusion layer in which Co diffuses into said diamond, and a Co layer.

17. (Withdrawn) A cutting tip according to claim 14, wherein said bonding layer includes a diffusion layer in which one or two or more metals selected from a group consisting of Ti, Zr, W, V, Nb, Ta, Cr, Mo, or Hf diffuses onto at least one of said cemented carbide or said diamond.

18. (Withdrawn) A cutting tip according to claim 14, wherein said diamond element is a high heat resistant sintered diamond including a binder phase of 0.1 to 15% by volume, where said binder phase is formed by one or two or more selected from the group consisting of carbonates of Mg, Ca, Sr, and Ba, oxides of Mg, Ca, Sr, and Ba, complex carbonates and complex oxide containing two or more thereof.

19. (Withdrawn) A cutting element for a drilling tool, comprising:
a cemented carbide post mounted on the tool body of the drilling tool; a diamond element supported by said post; and
a bonding layer formed between said post and said diamond element in order to bond them;
wherein said bonding layer includes a diffusion layer in which one or two or more metals selected from a group consisting of Fe, Ni, Co, Ti, Zr, W, V, Nb, Ta, Cr, Mo, and Hf diffuses onto at least one of said cemented carbide or said diamond.

20. (Withdrawn) A cutting element for a drilling tool, comprising:
a cemented carbide post mounted on the tool body of the drilling tool; and any of the cutting tips recited in claims 14 to 18; and wherein:
said cutting base of said cutting tip is mounted on said post.

21. (Withdrawn) A cutting tip for a drilling tool, comprising:

24. (Withdrawn) A drilling tool, comprising: a tool body; and
a cutting element provided in plurality on the distal surface of the tool body; and wherein:
said cutting element is the cutting tip recited in claim 19.

25. (Currently Amended) A bonding structure for a cemented carbide element and a diamond element according to claim 1, wherein said bonding layer comprising:

a first diffusion layer in which at least one metal selected from a group consisting of Fe, Ni, Co, Ti, Zr, W, V[[.]], Nb, Ta, Cr, Mo, and Hf diffuses into said cemented carbide;

a second diffusion layer in which said metal diffuses into the diamond; and

a metal layer comprising said metal that has not diffused.

26 (New) A bonding structure for a cemented carbide element and a diamond element according to claim 25, wherein:

said metal is selected from a group consisting of Fe and Ni;

said first diffusion layer has a thickness of 0.01 to 0.05 mm; and

said second diffusion layer has a thickness of 0.1 to 3 mm.

27 (New) A bonding structure for a cemented carbide element and a diamond element according to claim 25, wherein:

said metal is Co;

said first diffusion layer has a thickness of 0.005 to 0.2 mm;

said second diffusion layer has a thickness of 0.01 to 5 mm; and

said metal layer has a thickness of 0.01 to 0.2mm.

28 (New) A bonding structure for a cemented carbide element and a diamond element according to claim 25, wherein:

said metal is selected from a group consisting of Ti, Zr, W, V, Nb, Ta, Cr, Mo, and Hf

said first diffusion layer has a thickness of 0.002 to 0.05 mm;

said second diffusion layer has a thickness of 0.005 to 0.5 mm; and

said metal layer has a thickness of 0.01 to 0.2 mm.